

PMPB10XNE

20 V, single N-channel Trench MOSFET 30 November 2012

Product data sheet

Product profile 1.

1.1 General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- 2.2 kV ESD protection
- Small and leadless ultra thin SMD plastic package: 2 x 2 x 0.65 mm
- Exposed drain pad for excellent thermal conduction
- Tin-plated, 100% solderable side pads for optical solder inspection

1.3 Applications

- Charging switch for portable devices
- DC-to-DC converters
- Power management in battery-driven portables
- Hard disk and computing power management

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	20	V	
V_{GS}	gate-source voltage			-12	-	12	V	
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	-	12.9	Α	
Static characte	Static characteristics							
R _{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 9 \text{ A}; T_j = 25 ^{\circ}\text{C}$		-	10	14	mΩ	

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².



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Pinning information

Table 2. **Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol		
1	D	drain	1 6	D I		
2	D	drain	7 5 5 3 8 4 4 Transparent top view DFN2020MD-6 (SOT1220)			
3	G	gate		Transparent top view	$G \leftarrow G$	G / +
4	S	source				
5	D	drain				
6	D	drain		S 017aaa255		
7	D	drain				
8	S	source				

Ordering information 3.

Table 3. **Ordering information**

Type number	Package					
	Name	Description	Version			
PMPB10XNE	DFN2020MD-6	plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1220			

Marking 4.

Table 4. **Marking codes**

Type number	Marking code
PMPB10XNE	1H

Limiting values 5.

Table 5. **Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	20	V
V _{GS}	gate-source voltage			-12	12	V
I _D	drain current	$V_{GS} = 4.5 \text{ V}; T_{amb} = 25 \text{ °C}; t \le 5 \text{ s}$	[1]	-	12.9	Α
		V _{GS} = 4.5 V; T _{amb} = 25 °C	[1]	-	9	Α
		V _{GS} = 4.5 V; T _{amb} = 100 °C	[1]	-	5.7	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10$ μs		-	36	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[1]	-	1.7	W
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Symbol	Parameter	Conditions		Min	Max	Unit
		T _{amb} = 25 °C; t ≤ 5 s	[1]	-	3.5	W
		T _{sp} = 25 °C		-	12.5	W
T _j	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain	diode					•
I _S	source current	T _{amb} = 25 °C	[1]	-	2	Α
ESD maximum rating						
V _{ESD}	electrostatic discharge voltage	НВМ	[2]	-	2200	V

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

^[2] Measured between all pins.

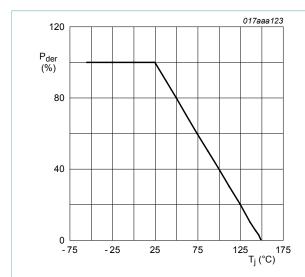


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

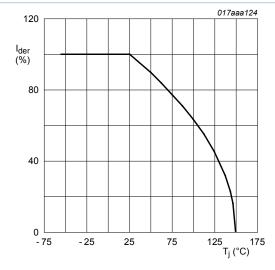


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

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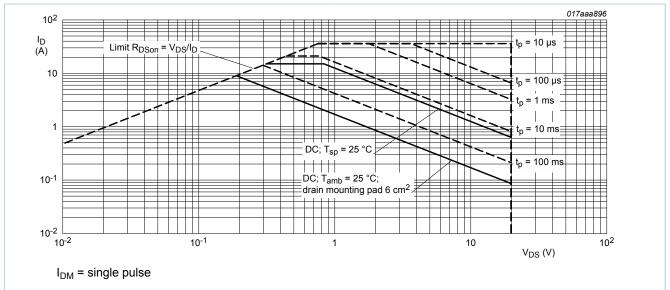


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance		[1]	-	235	270	K/W
	from junction to ambient		[2]	-	67	74	K/W
	ambient	in free air; t ≤ 5 s	[2]	-	33	36	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	5	10	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

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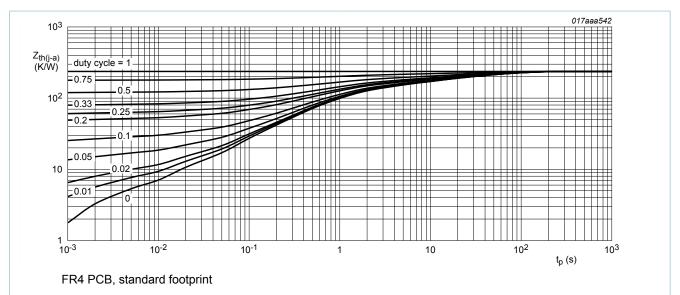


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

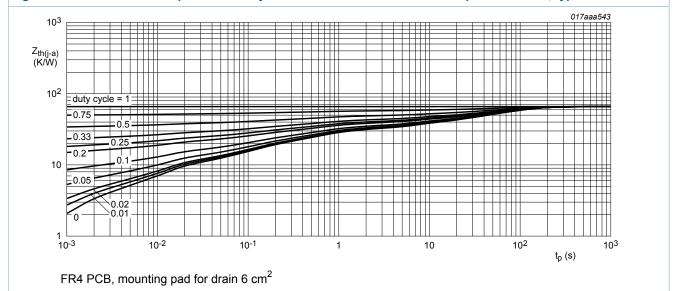


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

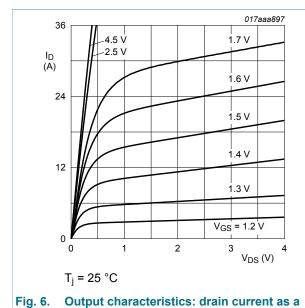
7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Static chara	Static characteristics							
$V_{(BR)DSS}$	drain-source breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C		20	-	-	V	
V_{GSth}	gate-source threshold voltage	$I_D = 250 \ \mu\text{A}; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}\text{C}$		0.4	0.65	0.9	V	
I _{DSS}	drain leakage current	$V_{DS} = 20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$		-	-	1	μA	
I _{GSS}	gate leakage current	V _{GS} = 8 V; V _{DS} = 0 V; T _j = 25 °C		-	-	10	μA	
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		$V_{GS} = -8 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	-10	μA
R _{DSon}	drain-source on-state	$V_{GS} = 4.5 \text{ V}; I_D = 9 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	10	14	mΩ
	resistance	V _{GS} = 4.5 V; I _D = 9 A; T _j = 150 °C	-	15	21	mΩ
		V _{GS} = 2.5 V; I _D = 8 A; T _j = 25 °C	-	12	18	mΩ
		V_{GS} = 1.8 V; I_D = 3.7 A; T_j = 25 °C	-	16	25	mΩ
9 _{fs}	forward transconductance	V _{DS} = 10 V; I _D = 9 A; T _j = 25 °C	-	60	-	S
R_G	gate resistance	f = 1 MHz	-	2	-	Ω
Dynamic c	haracteristics					'
Q _{G(tot)}	total gate charge	V_{DS} = 10 V; I_{D} = 6 A; V_{GS} = 4.5 V; T_{j} = 25 °C	-	23	34	nC
Q_{GS}	gate-source charge		-	2.6	-	nC
Q_{GD}	gate-drain charge		-	4.5	-	nC
C _{iss}	input capacitance	V _{DS} = 10 V; f = 1 MHz; V _{GS} = 0 V;	-	2175	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	235	-	pF
C _{rss}	reverse transfer capacitance		-	205	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 10 V; I_{D} = 6 A; V_{GS} = 4.5 V;	-	13	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	35	-	ns
$t_{d(off)}$	turn-off delay time		-	54	-	ns
t _f	fall time		-	50	-	ns
Source-dra	ain diode					
V _{SD}	source-drain voltage	I _S = 2 A; V _{GS} = 0 V; T _j = 25 °C	-	0.6	1.2	V



function of drain-source voltage; typical values

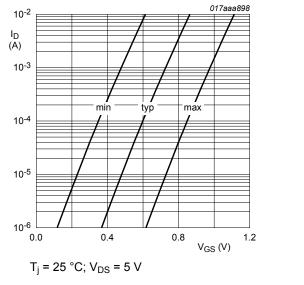


Fig. 7. Subthreshold drain current as a function of gate-source voltage

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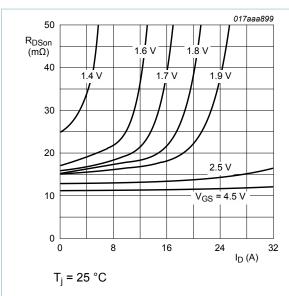


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

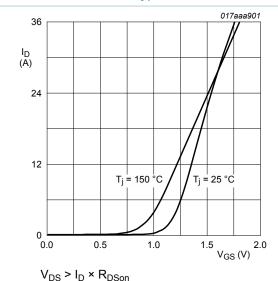


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

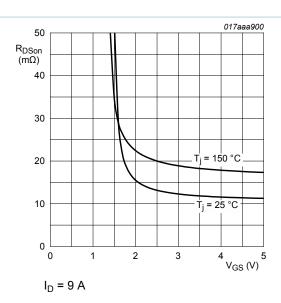


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

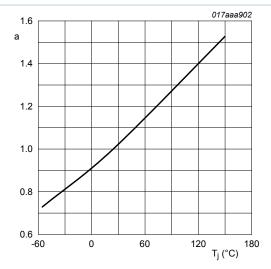


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

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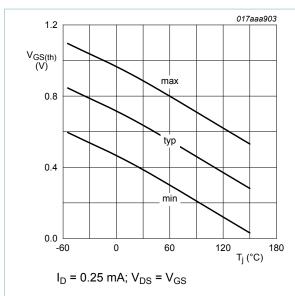


Fig. 12. Gate-source threshold voltage as a function of junction temperature

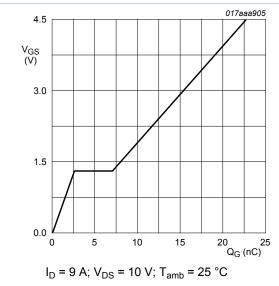


Fig. 14. Gate-source voltage as a function of gate charge; typical values

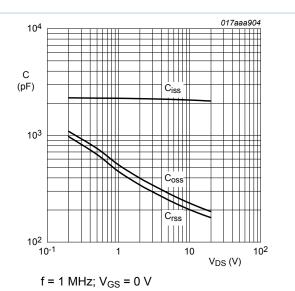


Fig. 13. Input, output and reverse transfer capacitances



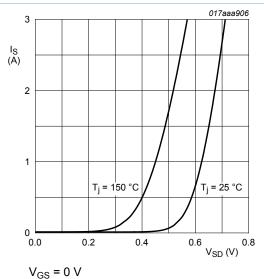
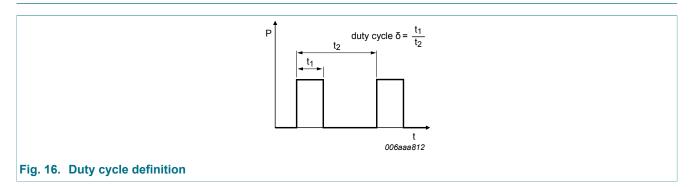


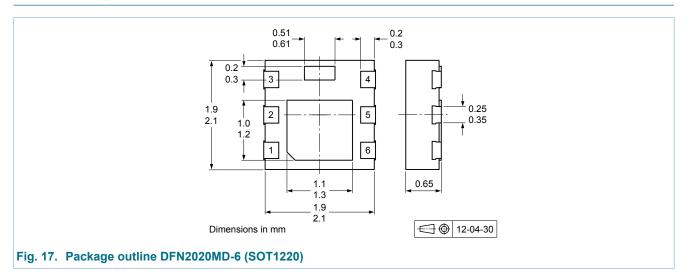
Fig. 15. Source current as a function of source-drain voltage; typical values

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8. Test information

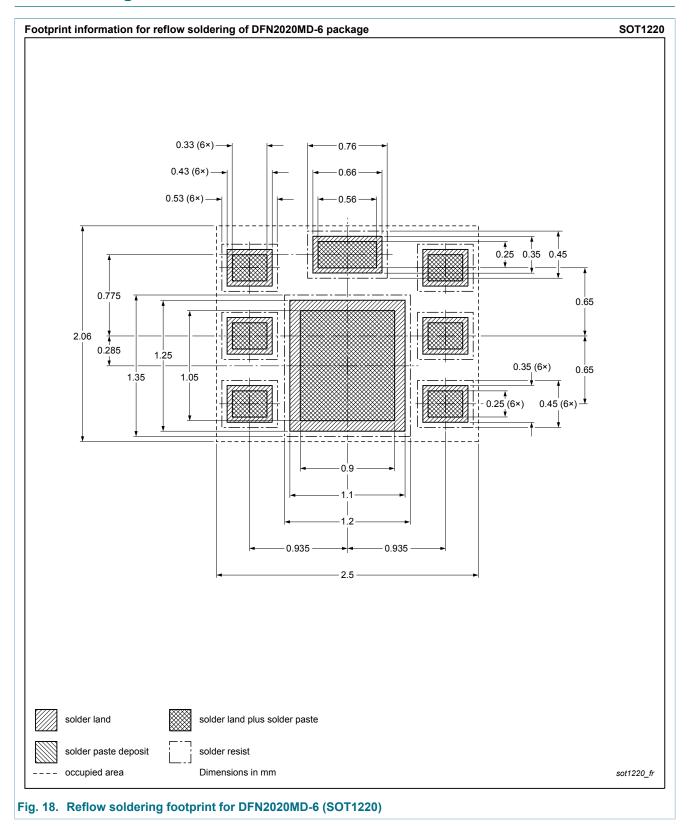


9. Package outline



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10. Soldering



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11. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMPB10XNE v.1	20121130	Product data sheet	-	-

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12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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